



**Is Now Part of**



**ON Semiconductor®**

**To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)**

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



March 2015

## FDD8444

### N-Channel PowerTrench<sup>®</sup> MOSFET

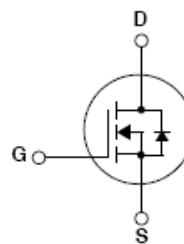
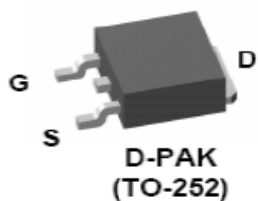
40V, 50A, 5.2m $\Omega$

#### Features

- Typ  $r_{DS(on)}$  = 4m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 50A
- Typ  $Q_{g(10)}$  = 89nC at  $V_{GS}$  = 10V
- Low Miller Charge
- Low  $Q_{rr}$  Body Diode
- UIS Capability (Single Pulse/ Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

#### Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems



**MOSFET Maximum Ratings**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	40	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current Continuous ( $V_{GS} = 10\text{V}$ ) (Note 1)	145	A
	Continuous ( $V_{GS} = 10\text{V}$ , with $R_{\theta JA} = 52^\circ\text{C/W}$ )	20	
	Pulsed	Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	535	mJ
$P_D$	Power Dissipation	153	W
	Derate above $25^\circ\text{C}$	1.02	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

**Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.98	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	52	$^\circ\text{C/W}$

**Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8444	FDD8444	TO-252AA	13"	16mm	2500 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

**Off Characteristics**

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{V}, T_J = 150^\circ\text{C}$	-	-	250	
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	2.5	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 50\text{A}, V_{GS} = 10\text{V}$	-	4	5.2	m $\Omega$
		$I_D = 50\text{A}, V_{GS} = 10\text{V}, T_J = 175^\circ\text{C}$	-	7.2	9.4	

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	6195	-	pF
$C_{oss}$	Output Capacitance		-	585	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	332	-	pF
$R_G$	Gate Resistance	$f = 1\text{MHz}$	-	1.9	-	$\Omega$
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	-	89	116	nC
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0$ to 5V	-	43	56	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V	-	11	14.3	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DD} = 20\text{V}$ $I_D = 50\text{A}$ $I_g = 1.0\text{mA}$	-	23	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	11	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	20	-	nC
			-			

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

**Switching Characteristics**

$t_{on}$	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 50\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 2\Omega$	-	-	135	ns
$t_{d(on)}$	Turn-On Delay Time		-	12	-	ns
$t_r$	Turn-On Rise Time		-	78	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	48	-	ns
$t_f$	Turn-Off Fall Time		-	15	-	ns
$t_{off}$	Turn-Off Time		-	-	95	ns

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 50\text{A}$	-	0.9	1.25	V
		$I_{SD} = 25\text{A}$	-	0.8	1.0	
$t_{rr}$	Reverse Recovery Time	$I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	39	51	ns
$Q_{rr}$	Reverse Recovery Charge		-	45	59	nC

**Notes:**

- 1: Package current limitation is 50A.  
 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.67\text{mH}$ ,  $I_{AS} = 40\text{A}$

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>

All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

## Typical Characteristics

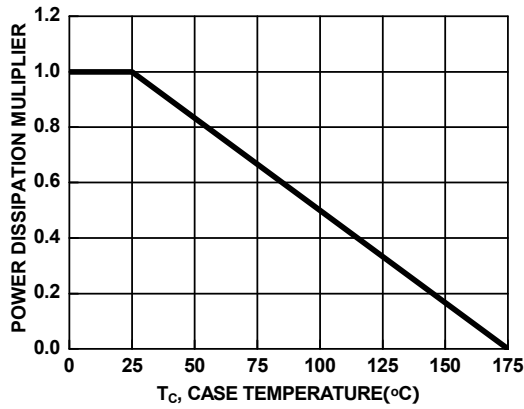


Figure 1. Normalized Power Dissipation vs Case Temperature

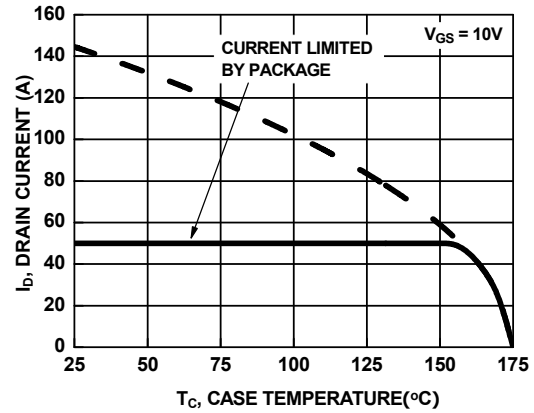


Figure 2. Maximum Continuous Drain Current vs Case Temperature

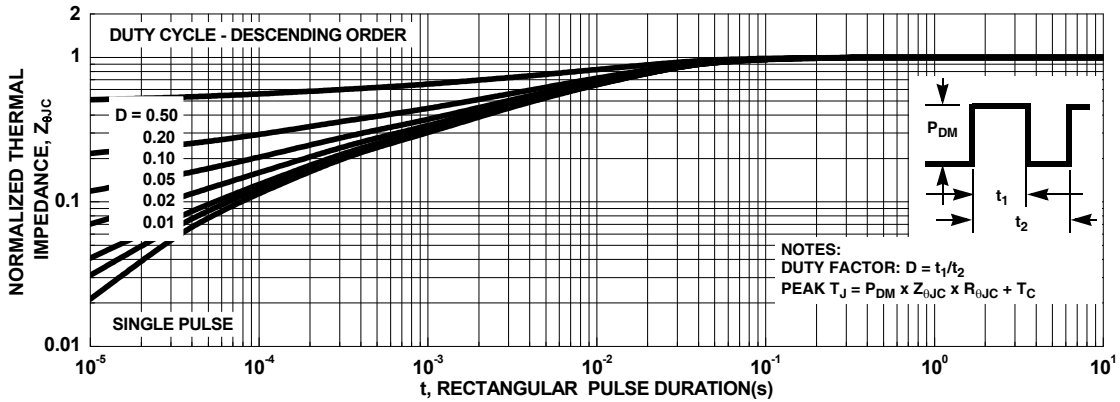


Figure 3. Normalized Maximum Transient Thermal Impedance

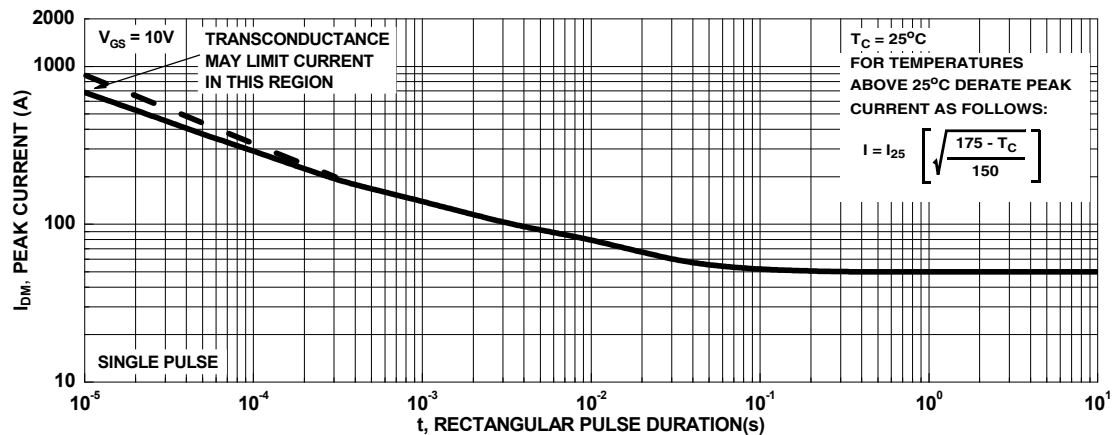


Figure 4. Peak Current Capability

## Typical Characteristics

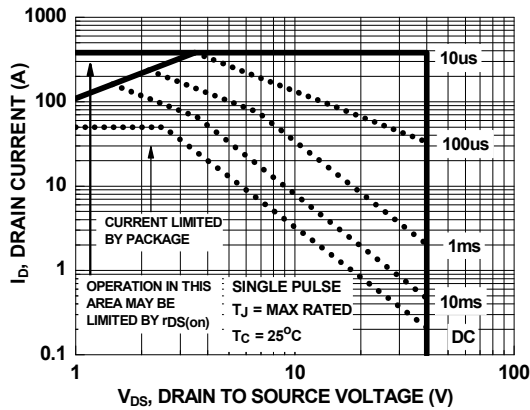
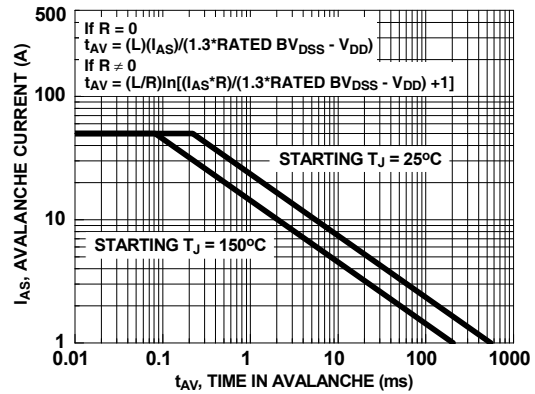


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

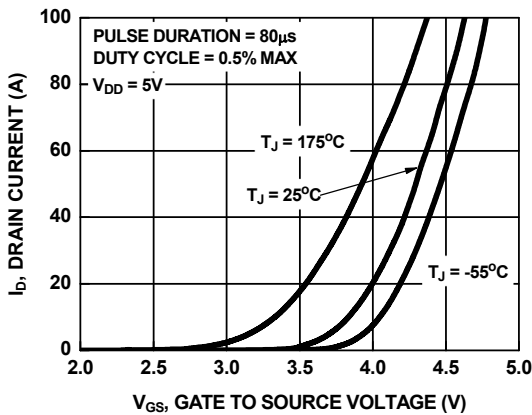


Figure 7. Transfer Characteristics

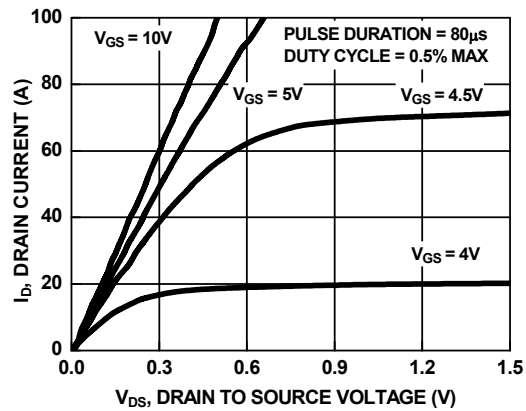


Figure 8. Saturation Characteristics

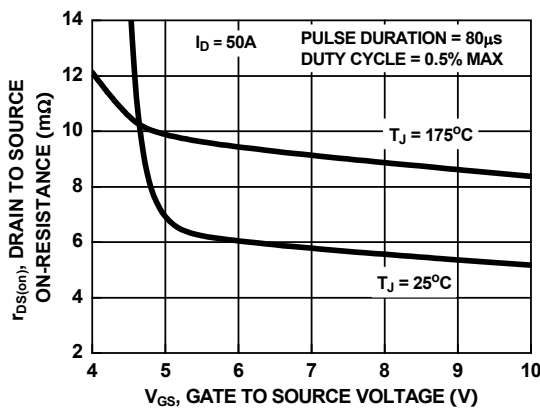


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

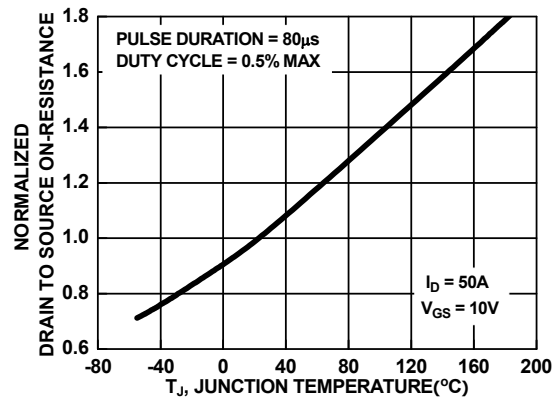


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

## Typical Characteristics

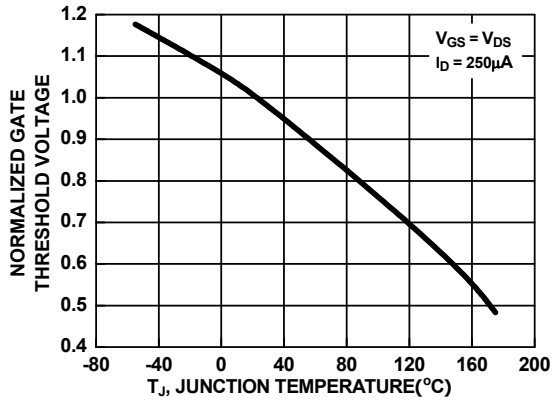


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

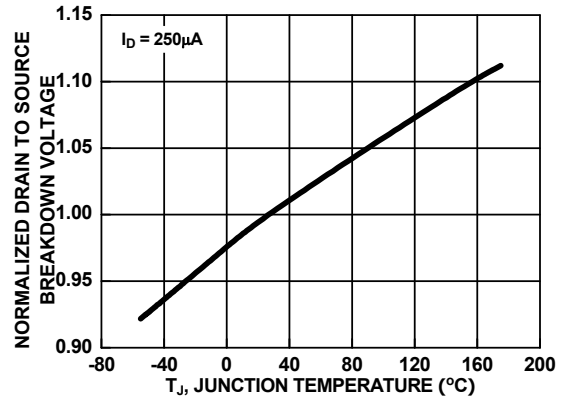


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

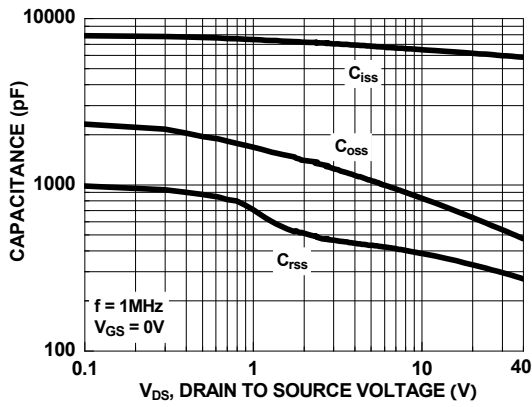


Figure 13. Capacitance vs Drain to Source Voltage

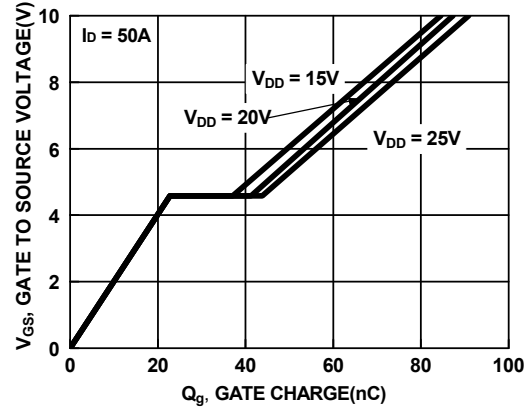
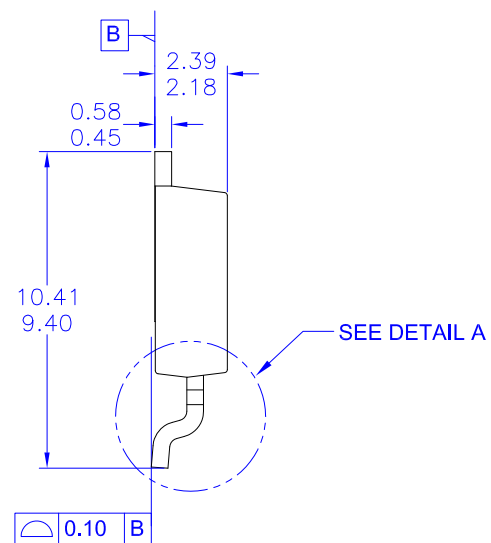
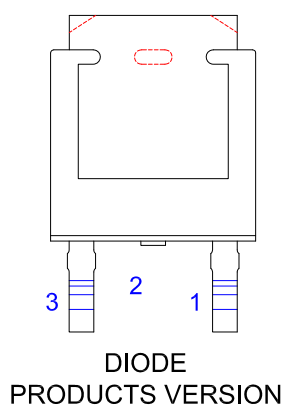
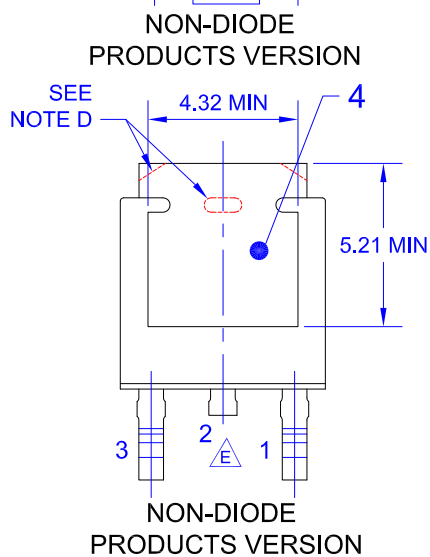
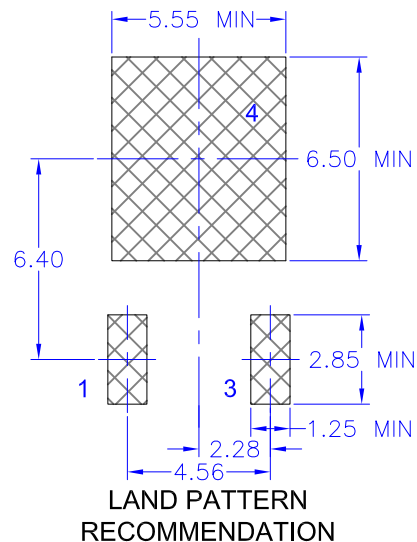
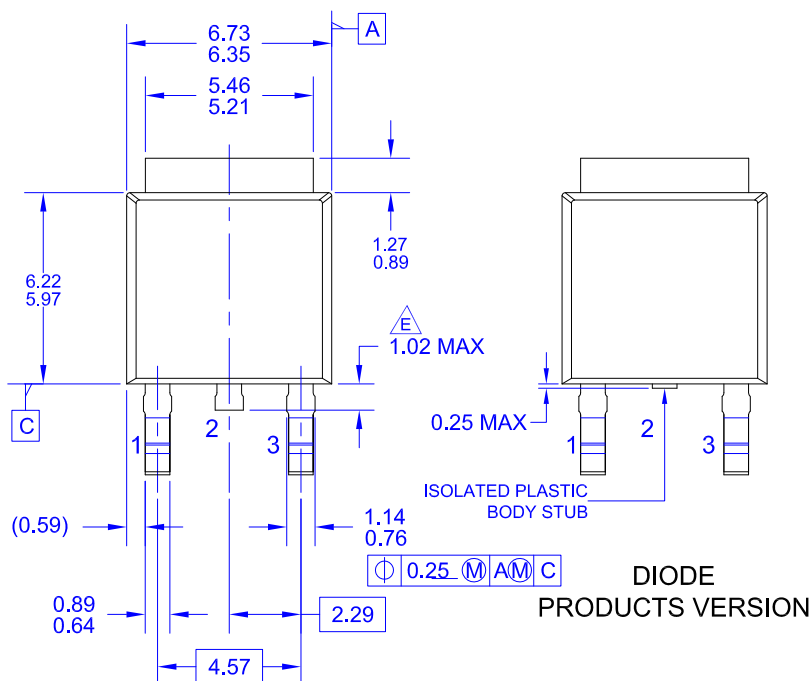


Figure 14. Gate Charge vs Gate to Source Voltage



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

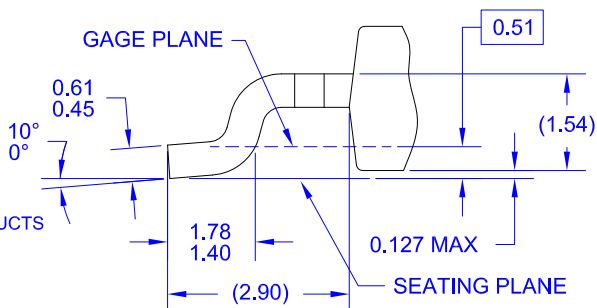
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A  
(ROTATED -90°)  
SCALE: 12X







## TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™  
AttitudeEngine™  
Awinda®  
AX-CAP®  
BitSiC™  
Build it Now™  
CorePLUS™  
CorePOWER™  
CROSSVOLT™  
CTL™  
Current Transfer Logic™  
DEUXPEED®  
Dual Cool™  
EcoSPARK®  
EfficientMax™  
ESBC™  
F®  
Fairchild®  
Fairchild Semiconductor®  
FACT Quiet Series™  
FACT®  
FastvCore™  
FETBench™  
FPS™  
F-PFS™  
FRFET®  
Global Power Resource™  
GreenBridge™  
Green FPS™  
Green FPS™ e-Series™  
Gmax™  
GTO™  
IntelliMAX™  
ISOPLANAR™  
Making Small Speakers Sound Louder and Better™  
MegaBuck™  
MICROCOUPLER™  
MicroFET™  
MicroPak™  
MicroPak2™  
MillerDrive™  
MotionMax™  
MotionGrid®  
MTI®  
MTx®  
MVN®  
mWSaver®  
OptoHiT™  
OPTOLOGIC®

OPTOPLANAR®  
Power Supply WebDesigner™  
PowerTrench®  
PowerXS™  
Programmable Active Droop™  
QFET®  
QS™  
Quiet Series™  
RapidConfigure™  
Saving our world, 1mW/W/kW at a time™  
SignalWise™  
SmartMax™  
SMART START™  
Solutions for Your Success™  
SPM®  
STEALTH™  
SuperFET®  
SuperSOT™-3  
SuperSOT™-6  
SuperSOT™-8  
SupreMOS®  
SyncFET™  
Sync-Lock™

SYSTEM GENERAL®  
TinyBoost®  
TinyBuck®  
TinyCalc™  
TinyLogic®  
TINYOPTO™  
TinyPower™  
TinyPWM™  
TinyWire™  
TranSiC™  
TriFault Detect™  
TRUECURRENT®  
μSerDes™  
SerDes®  
UHC®  
Ultra FRFET™  
UniFET™  
VCX™  
VisualMax™  
VoltagePlus™  
XS™  
Xsens™  
仙童®

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT [HTTP://WWW.FAIRCHILDSEMI.COM](http://www.fairchildsemi.com). FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

## AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

## ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, [www.fairchildsemi.com](http://www.fairchildsemi.com), under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I77